



Fast Pressure Prediction with a MEMS Pirani Sensor for Protection of MOMA-MS

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MOMA MS has two ion sources, an (1) El source and (2) an LDI source.



Definition:

Static mode: El source (1) is used and gas composition is helium at 3 mtorr. **Dynamic mode:** LDI source (2) is used and gas composition is mostly mars mix at pressures between 60 mtorr and <0.1 mtorr

^{A.Southard 9/15/2015} *Anal Chem. 2008 Jun 1;80(11):4026-32. doi: 10.1021/ac800014v. Epub 2008 May 8²



The pressure must be kept low to protect the filament (static mode) and high voltage supplies (dynamic mode)

MOMA-MS includes several elements requiring high voltges that are sensitive to overpressure



Components:



Filament

Problem with overpressure



Reduced lifetime

High voltage supplies:

• Dynode

Channeltron
multiplier

• Rods of the LIT

Arc discharge followed by failure of the power supply

Pump

Reduced lifetime



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Timing diagram during dynamic mode: After the aperture valve closes, the pressure must get below 0.5 mtorr before the RF voltage can ramp (during the resonant ejection process). When SWIFT is used response time must be even shorter (not shown below).



Actual pressure variation during dynamic mode (using reference gauge)



Valve Opening Time	Max Pressure	Pump down Time to 0.5mTorr
80ms	30mTorr	0.65secs
250ms	60mTorr	0.75secs
500ms	90mTorr	0.85secs
1000ms	95mTorr	0.9secs

Pump down time as low as 0.65 s





MOMA linear ion trap



It would be problematic if MOMA-MS should have a pressure sensor larger than its ion



BA gauge



A.Southard 9/15/2015 >33 mm Capacitance Manometer or diaphragm gauge

trap



>50 mm

(Heimann) MEMS pirani sensor

Package (TO39) with lid Package without lid







Miniature thermal conductivity gauges are the ones best suited for fine to high vacuum pressure measurements

а

glass

substrate

Miniature diaphragm gauges use the change of capacitance (or field emission from below) due to diaphragm deformation

Micromechanical torsion resonator gauges use the influence of gas pressure on the resonant frequency of an oscillating system

3E-3 to 3E-2 torr NEG Al electrode cavity Hemni H, Shooji S, Yosimi K, Esashi M. Transducers'93, In: Seventh international conference on solid-state sensors and actuators, Denki-Gakkai Proc; 1993. p. 584. Oscillator Spring Chipframe Electrode 1 Example Note: Substrates are 4" Carrier Electrode 2 Hole Electrode 3 Vacuum D. Tenholte, S. Kurth, T. Geßner, W. Dötzel, http://dx.doi.org/10.1016/j.sna.2007.05.031.

Al electrode on Si membrane

Miniature thermal conductivity gauges

conductivity gauges use the change of gas thermal conductivity and convection with pressure (commercially available from A.Southard 9/15/2015 MKS, Heimann, Xensor) Unusual Example

Example



Note: Great pressure range 7.5 E-6 to 760 torr.

Note:

Pressure range:

M. Kimura, F. Sakurai, H. Ohta, T. Terada. Microelectronics Journal, 38 (2) (2007), pp. 171–176



Volklein's carefully optimized MEMS pressure sensors can detect pressure variations from 1E-6 to 10 torr



Researcher	Type of	gauge	Pressure range (Torr)		
Van Herwaarden, Sarro, 1988 ¹	Heated cantilever combined with them	Heated cantilever combined with thermopile			
Völklein and Schnelle, 1991 ²	Heated resistor combined with thermo	Heated resistor combined with thermopile (Bi resistor, Bi/Sb thermopile)			
Mastrangelo and Muller, 1991 ³	Microbridge (poly-Si beam)	Microbridge (poly-Si beam)			
Robinson et al., 1992 ⁴	Resistor on dielectric membrane (poly	Resistor on dielectric membrane (poly-Si)			
Swart et al., 1994 ⁵	Microbridge (poly-Si)	Microbridge (poly-Si)			
Paul et al., 1994 ⁶	Resistor on dielectric membrane (poly	r-Si)	$7.5 \cdot 10^{-1} - 7.5 \cdot 10^{+2}$		
Shie et al., 1995 ⁷	Resistor on dielectric membrane (plati	inum) — I — I	10^{-7} -1 ^a		
Chuo et al., 1997 8	Resistor on dielectric membrane (plati	num)	$10^{-1} - 10^{+5}$		
Stark et al., 20039	Resistor on dielectric membrane (plati	num)	$10^{-2} - 10^{+3}$		
De Jong <i>et al.</i> , 2003 ¹⁰	Resistor on dielectric membrane (plati	num)	$7.5 \cdot 10^{-2} - 150$		
Chae et al., 2004 ¹¹	Microbridge (p++ silicon coil)		$2 \cdot 10^{-2} - 2$		
Moelders et al., 2004 ¹²	Microbridge	Note: The lower limit of	$10^{-2}-1$		
Doms et al., 2005 ¹³	Microbridge (platinum beam)	pressure range depends on	$7.5 \cdot 10^{-1} - 7.5 \cdot 10^{+2}$		
Stark et al., 200514	Microbridge (poly-Si beam)	noise reduction Given a	$10^{-2} - 7.5 \cdot 10^{+3}$		
Zhang et al., 2006 ¹⁵	Resistor on dielectric membrane	signal of 100 w// Chie/e actual	$7.5 \cdot 10^{-2} - 7.5 \cdot 10^{+2}$		
Mitchell et al., 2008 ¹⁶	Microbridge (poly-Si beam)	signal of 100 μ V, shie's actual	$10^{-2} - 7.5 \cdot 10^{+2}$		
Khosraviani and Leung, 2009 ¹⁷	Microbridge (nichrome film)	lower limit <mark>(1)</mark> is 4E-5 torr .	$10^{-1} - 7.5 \cdot 10^{+3}$		
Qui et al., 2009 ¹⁸	Metallic wire	The lowest lower limit. 1E-6	$7.5 \cdot 10^{-3} - 7.5 \cdot 10^{-1}$		
Li et al., 2010 ¹⁹	Microbridge	torr is provided by Heimann	$8 \cdot 10^{-2} - 2 \cdot 10^{+2}$		
Jiang <i>et al.</i> , 2010 ²⁰	Microbridge		$7.5 \cdot 10^{-4}$ -7.5		
Schlecher et al., 2011 ²¹	Ni-microbeam	(3)	$2.25 \cdot 10^{-2} - 7.5 \cdot 10^{+2}$		
Wang et al., 2011 ²²	W-microplate		$7.5 \cdot 10^{-4} - 7.5 \cdot 10^{+2}$		
Santagata et al., 2011 ²³	Tube-shaped	2	$10^{-3} - 10^{+3}$		
Mercier et al., 2012 ²⁴	Cr/Au-resistor on LiNbO3-substrate (S	SAW-device)	$7.5 \cdot 10^{-6} - 7.5 \cdot 10^{+2}$		
Chen, 2012 ²⁵	Microbridge	3	$1 - 10^{+3}$		
Present paper	▶ 🖑 ⊖ ⊕ 142% ▾ 🕒		$1 \cdot 10^{-6} - 10$		
A.Southard 9/15/2015 Volklein J. Vac. Sci. Technol. A 31, 061604 (2013)					



How to determine pressure using a pirani sensor by determining two temperatures



Concept:

The loss of heat through gas conduction is proportional to pressure.

Monitoring the temperature of an electrically heated membrane enables the determination of the pressure.

Non-equilibrium heat equation (equilibrium version provided by Volklein et al. (2013)): Note: Heimann optimized membrane geometry and materials to reduce P_r and P_{sc}





(Heimann) MEMS pirani

9.2 mm

Determining temperatures with the Heimann mems pirani sensor:

The membrane temperature and ambient temperature are found by measuring the resistance of the membrane heater, $R_p(p, T)$, and a second resistor thermally sunk to the heat sink, $R_k(T_0)$.

Picture of membrane with electrical

Equivalent circuit: Measuring voltage V_k and current A give resistances



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2.1 V

Note: Power use $< 200 \mu$ Watts. Using matched temperature coefficients helps to control for ambient temperature variation

Heimann's suggested use









How to deal with slow response of the Heimann mems pirani sensor (model HVS-03k)

Obstacle:

Response is slow due to heat capacity of membrane



Solutions:

The full, non-equilibrium heat equation must be solved. Sensor to sensor variability even among the same batch requires calibration of G_c , \mathcal{E}_{eff} , C, and γ to achieve the target pressure accuracy over ambient temperature and for the two important gases used with MOMA helium and mars mix

$$p = \frac{1}{\gamma T_0^{(-0.5)} * A * (T - T_0)} \left(N - C \frac{dT}{dt} - G_c(T - T_0) - 2\sigma A \varepsilon_{eff} \left(T^4 - T_0^4 \right) \right)$$

Since the lower limit of pressure detection strongly dependent on electrical noise (thermal, EMI), digital and analog filtering required to deal with derivative term.

Calibrations process starts with (1) 2nd order dependence of resistance on temperature for both resistors in an oven.

Oven setup for Resistancetemperature correlation Note: Source small 10 µA current to avoid self-heating and measure/voltage drops.





At low pressure (~1e⁻⁶ Torr), thermal equilbrium

$$N = G_{c}(T - T_{0}) + 2\varepsilon_{eff}A * \sigma \left(T^{4} - T_{0}^{4}\right)$$

N is the heating power, A is the membrane area, and σ is the Stefan-Boltzmann constant.

At T₀=293 K, we can vary T and N by changing the applied voltage. We can then fit the right side of the equation to the calculated heating power by treating Gc & ε_{eff} as free parameters



Fits routinely achieve R² of 0.99999

Note:

The graph to the right was obtained with a voltage sweep up to 2.7 V. Experiments done by us and Heimann would later suggest that device failure was occurring due to thermal stress and lower bias voltages must be used.



The scaling factor γ is found by sweeping pressure and scaling results

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Concept:

The scaling factor γ depends on the mass of the gas molecule and the accommodation coefficient, a measure of how effective energy transfer is at the surface of the membrane

Procedure to determine γ :

Use a baratron reference gauge to vary pressure from ~1e⁻⁶ Torr to 0.1Torr and choose γ to match the reference pressure at reference pressure of 0.01 torr (under equilibrium conditions).

Note: This is done for both helium and mars mix. These methods provide information about surface physics.





Using smoothing and averaging to determine heat capacity



Method:

The heat capacity is determined by pulsed calorimetry: Under high vacuum, the sensor is powered on abruptly at an ambient temperature of 293 K and voltage & current measurements are taken as the sensor heats up

Signal processing steps:

- 1) All power terms are smoothed with a centered moving average
- 2) Five experiments are synced and averaged to improve S/N
- 3) The resulting average heat capacity vs. *T* is twice smoothed with a centered moving average and fit with a first order equation in T





Coefficients determined from linear fit

C=C1+C2*T Typical values: 2 C1=2E-6 J/K, C2=5E-9 J/K



Predicting helium pressure at -30 and GESTAR 80 °C

Ambient temperatures on MOMA can vary from -30 to 80 °C

Requirements:

•0.1 mtorr accuracy in the 0.1 to 1 mtorr regime

•20% accuracy in the 1 to 50 mtorr regime

 $T_0 = -30 \,^{\circ}C$ 0.1 torr baratron (torr) 0.1 torr baratron (torr) Smoothed predicted pressure (torr) Smoothed predicted pressure (torr) meet requirements (1 for yes/0 for no) meet requirements (1 for yes/0 for no) 1 1 meet requirements (1 for yes/0 for no) meet requirements (1 for yes/0 for no) 0.1 1.0 1.0 0.1 Pressure(torr) Pressure(torr) 0.01 0.01 1E-3 0.5 1E-3 0.5 1E-4 1E-4 1E-5 0.0 1E-5 200 400 800 1000 1200 1400 600 0 200 400 800 1000 1200 0 600 time (seconds) time (seconds) A.Southard 9/15/2015 16

 $T_0 = 80 °C$



Improving low pressure prediction by accounting for ambient temperature dependence of Gc & ε_{eff}



Low pressure prediction can be improved by using the second order fit to predict pressure





Predicting dynamic changes in mars mix pressure at 20 °C



Initial use of the dynamic algorithm without any post-processing applied demonstrated that the reference gauge response was less noisy but lagging behind by 0.09 s.



Note:

Here the green line indicates we are meeting our accuracy requirements: 0.2 mtorr accuracy in the 0.1 to 1 mtorr regime, and 20% from 1-50 mtorr





Predicting dynamic changes in mars mix pressure at -30 and 80 °C



Again, while pressure predictions meet requirements, predicted pressure is lower than true below 0.1 mtorr



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Increasing voltage increases sensitivity but can lead to device failure



 100 µm
 EHT = 20.00 kV
 Mag = 143 X
 Signal A = SE2
 Ahmed Amin

 WD = 9.5 mm
 File Namo = Laser Cover Laser Cove

"Blisters" formed on membrane due to overpowering at bias of 2.7 V





Life tests revealed that prolonged biasing at 2.7 V could impact usable lifetime

Number of gauges	Bias voltage
15	1.5
10	2.1
5	2.6

A lifetest was conducted to determine whether overpowering could be an issue:

Definition: Wear = Resistance drift normalized by initial resistance and compensated for ambient temperature swings Drift in the 2.6 V batch was a greater fraction of the tolerated allowance and too great to reach 2x life

Biasing at 2.1 V lead to an acceptable drift in every phase of the experiment. This was consistent with suspected overpowering at a bias of 2.7 V. The most stressful condition for the 2.1 V group was at 100 °C.

Testing phase	Duration	
800 power cycles @ -50 C	NA	
Soak @ -50 C	550 hours	
Soak @ 100 C	1010 hours	



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Lifetest Test Results

- Flight gauges had slightly lower nominal resistances (7 kohm instead of 8 kohm for the ETU gauges) so a high temperature soak was performed with them
- 9 flight gauges tested at 100 C for 950 hours
- Failure criteria: sense resistance change compensated for ambient temperature drift < resistance change at 80 °C when pressure changes from 0.1 to 0.2 mtorr.









A simple model was adapted to predict pressure with a MEMS pirani sensor from Heimann by determining physical properties of the sensor through a set of experiments. This resulted in an algorithm to predict pressure over operational temperatures from -30 to 80 °C, helium and mars mix gas compositions, and has a response time of 50 ms.

Accuracy was targeted to be within 0.1 mtorr of the reference in the sub-mtorr regime and within 20% otherwise.

In dynamic mode, accuracy was targeted to be 0.2 mtorr in the sub-mtorr regime most crucial to timing power-on of MOMA high voltage power supplies.



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